EXHIBIT F

TO RULE 4.2 STATEMENT OF DR. DOUGHERTY

Boston • London Artech House

CAPACITANCE, INDUCTANCE, AND CROSSTALK ANALYSIS k of Microwave Testing, Thomas S. Laverghetta er Microwave Sources, Victor Granalstien and Igor Alexess, eds. k for the Mechanical Tolerancing of Waveguide Components. k of Microwave Integrated Circuits, Reinmut K. Hoffmann th Helical and Folded Helical Resonators, Peter Vizmuller megrated Circuits, P. Bhartia and P. Pramanick, eds. Arsenide Processing Techniques, Ralph Williams SFET Circuit Design, Robert A. Soares, ed.

Design, and Applications of Fin Lines. Bharathi Bhat and

Lossy Line Calculation Software and User's Manual, Fred. E.

ion to Microwaves, Fred E. Gardiol

Charles S. Walker

Transition Design, Jamal S. Izadian and Shahin M. Izadian ectrum Analyzer Theory and Applications, Morris Engelson e Engineer's Handbook: 2 volume set, Theodore Saad, ed. es Made Simple: Principles and Applications, Stephen W. Lines and Stotlines, K.C. Gupta, R. Garg, and I.J. Bahl Microwave Integrated Circuits: Technology and Design, Digital Microwave Communications, Ferdo Ivanek, et al. e Fillers, Impedance Matching Networks, and Coupling and Millimeter Wave Heterostructure Transistors and Handbook for Hybrid Microelectronics, J.A. King, ed. ! Integrated Circuits, Jeffrey Frey and Kul Bhasin, eds. ign: GaAs FET's and HEMT's, Peter H. Ladbrooke Antenna Design, K.C. Gupta and A. Benalla, eds. res, G.L. Matthaei, L. Young and E.M.T. Jones Transmission Line Couplers, J.A.G. Malherbe Transmission Line Filters, J.A.G. Malherbe Vicrowave Circuits, Stephen A. Maas nsmission Lines, Fred E. Gardiol Frederick H. Levien, et al. Mixers, Stephen A. Maas Tubes, A.S. Gilmour, Jr. tions, F. Ali, ed.

Library of Congress Cataloging-in-Publication Data

Walker, Charles S.

Capacitance, inductance, and crosstalk analysis / Charles S.

Walker.

Ġ

Includes bibliographical references.

ISBN 0-89006-392-3

1. Electric circuits. 2. Electric inductors. 3. Capacitors.

4. Crosstalk. I. Title.

621.319'21--dc20 TK454.W36

90-252 CH

British Library Cataloguing in Publication Data

Walker, Charles S.

Capacitance, inductance, and crosstalk analysis.

1. Electromagnetism

ISBN 0-89006-392-3

© 1990 ARTECH HOUSE, Inc.

Norwood, MA 02062 685 Canton Street

All rights reserved. Printed and bound in the United States of America. No part of this publication may be reproduced or utilized in any form or by any means, electronic or mechanical, including photocopying, recording, or by any information storage and retrieval system, without permission in writing from the publisher.

International Standard Book Number: 0-89006-392-3 Library of Congress Catalog Card Number: 90-252

* w 9 ٣œ 9 2 $Z_{to} = \sqrt{\frac{L_1}{C_1}} \Omega \tag{36}$

and

$$\sqrt{\frac{(L_1/I)(C_2/I)}{(L_1/I)(C_1/I)}} = \sqrt{\frac{\mu\varepsilon}{\mu\varepsilon}} = 1$$
 (37)

Substituting Eqs. (35), (36) and (37) into Eq. (32) yields Eq. (29):

$$C_m = \frac{L_m}{Z_{01}Z_{02}} \, F/m$$

REFERENCES

- 1. Boast, William B., Principles of Electric and Magnetic Pields, New York, Harper and Brothers,
- 1956, pp. 205-210, 229, 311.
 2. Moht, R.J., "Coupling between Open Wires over a Ground Plane," IEEE Symp. on EMC, July 22-25, 1968, pp. 404-413.

2.2.4 Capacitance between Parallel, Vertical, Flat Conductors, C-4

This formula set introduces the concept of fringing flux. This is an important consideration because fringing increases the value of the capacitance between parallel vertical conductors above that calculated neglecting fringing, often by many times. Please see Formula Set C-6 for the derivation of the fringing factor. An important application is the determination of the capacitance between lands on printed wiring boards such as those shown in Fig. 2.10.

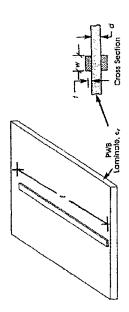


Figure 2.10 Parallel, flat conductors are located on opposite sides of a PWB at a distance d apart.

Equations:

The value of capacitance per unit length is defined as $\frac{C}{l} \approx \epsilon_r \epsilon_0 K_{Cl} \left(\frac{\nu}{d}\right) F/m$ $= 8.84 \epsilon_r K_{Cl} \left(\frac{\nu}{d}\right) PF/m$ $= 0.225 \epsilon_r K_{Cl} \left(\frac{\nu}{d}\right) PF/m$

9

ਰ

where $K_{\rm Cl} = {
m Capacitive}$ fringing factor (1 or greater). For $d/w \ll 1, \, K_{\rm Cl} = 1.$

Fringing Flux:

As previously noted, flux fringing increases the value of the capacitance. Figure 2.1 illustrates this idea with a sketch plotting the approximate flux patterns for a paralle plate capacitor with and without fringing.

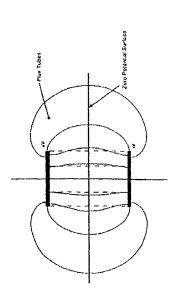


Figure 2.11 The dimensions for this parallel plate capacitor are chosen to show a capacitance increased due to fringing of 2.5 times. Flux lines without fringing are shown disched. This sketch of the flux apparent shows a total of 19 flux tubes (versus 4 in the dashed line case). Thus the capacitance is 2.5 times greate. (The surrounding nection has a relative dielectric constant, v, = 1 and is thus homogeneous for this specific case.)

20

Example:

Determine the capacitance between two vertical conductors as shown in Fig. 2.10 with these dimensions:

$$l = 0.0028^a$$
 (2 oz. copper) $d = 0.060^a$
 $w = 0.025^a$ $l = 6^a$

Assume that a printed wiring board with epoxy-glass laminate with a relative dielectric constant $\epsilon_r = 4.5$. Sep 1: Using Fig. 2.12, determine the fringing factor, K_{C1} , for $d/w = 0.060^\circ/0.025^\circ = 2.4$.

Step 2: Determine the capacitance from Eq. (2b) above.

$$C = 0.225 \, e_r K_{c1} \left(\frac{w}{d} \right) \times l \, pF$$

$$= 0.225 \times 4.5 \times 2.4 \times \left(\frac{0.025^*}{0.060^*} \right) \times 6^* \, pF$$

$$= 6.1 \, pF$$

The measured value for this example was 6.4 pF showing excellent correlation.

Perivation:

(Please refer to Formula Set C-6.)

Commentary and Conclusions:

- 1. This formula sot graphically illustrates the effect of fringing on "parallel" plate capacitors. Figure 2.12 indicates that for d/w = 16, the actual expacitance is 7.9 times greater than would be predicted from direct parallel plate equations, neglecting fringing. This increase could mean the difference between achieving or not neeting the crosstalk requirements.
- or not needing the crosstalk requirements.

 2. In most PWB designs the land width dimensions, w_i are about the same or smaller than the thickness of the circuit boards. For example, for 0.000° thick board and a trace with $w = 0.020^{\circ}$, d/w = 3 (which is not $\ll 1$). Thus, electric flux fringing cannot be ignored.

Figure 2.12 The fringing factor, K_{c_1} , is determined by entering the graph at the ratio d/w, proceeding upward to the curve and locating K on the left-kand vertical axis as indicated. Thus, for d/w = 2.4, $K_{c_1} = 2.4$. (This figure was developed in Formula Set C-6.)

2.2.5 Capacitance between Horizontal Flat Conductors, C-5

ô

The capacitance value between horizontal, rectangular conductors is important because this configuration closely approximates conductor lands on printed wiring boards such as those shown in Fig. 2.13.

Equations:

The capacitance per unit length is given approximately by

$$\frac{C}{l} \approx \frac{\pi e_{telt} \rho_0}{\ln \left(\frac{\pi (d - W)}{w + l} + 1\right)} F/m \tag{1}$$

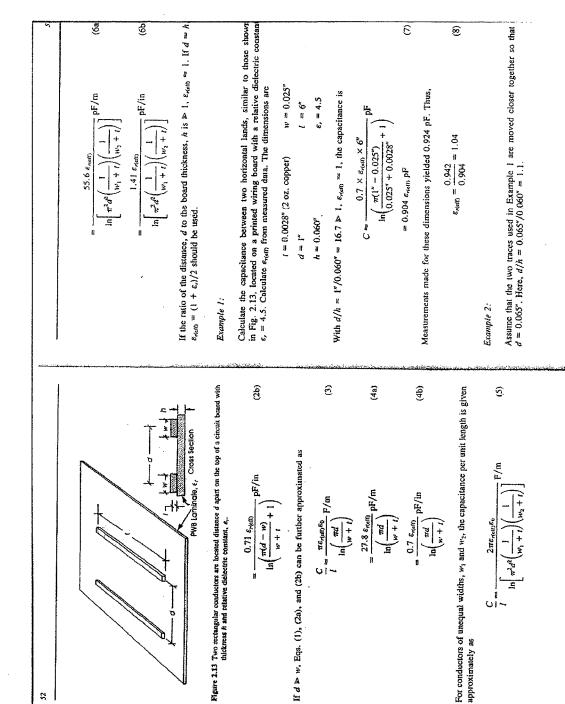
(S

 $\ln\left(\frac{\pi(d-w)}{w+1}+1\right)$

\$2

= 27.8 Enelly pF/m

 $\ln\left(\frac{\pi d}{v + t}\right)$



If $d \gg w$, Eqs. (1), (2a), and (2b) can be further approximated as

 $\ln\left(\frac{n(d-w)}{w+t}+1\right)$

 $\frac{C}{l} = \frac{\pi e_{r(eff)} e_0}{l} F/m$

 $\ln\left(\frac{\pi d}{w+t}\right)$

	Š	6
$C \approx \frac{0.7 \times \epsilon_{\text{rem}} \times 6^{\circ}}{10.065^{\circ} - 0.025^{\circ}}$ pF	= 2.49 E. D. WOTEN 5 41 nF manned	The state of the s

The measured effective dielectric constant in this case then, is

$$s_{reff} = \frac{5.41}{2.49} = 2.17$$

3

Equation Development:

Equation (1) is adapted from Eq. (2), Formula Set C-1, where

$$\int_{\mathbb{R}^{2}} \frac{\pi^{6/\epsilon_0 n} \epsilon_0}{\ln \binom{d}{r}} F/m, \quad \text{for } \frac{2r}{d} \leqslant 1$$

 Ξ

By making the perimeter of the round conductor equal to that of the rectangular conductor we will get equal surface areas per unit length for the two geometries:

Perimeter =
$$2\pi\tau = 2(w+t)$$
 (12)

Substituting r into Eq. (11) gives

$$\frac{C}{l} = \frac{\tau e_{o,tn} \epsilon_o}{\ln \left(\frac{\pi d}{m + l}\right)} F/m, \quad \text{for } \frac{2(w + t)}{m d} \leqslant 1 \tag{14}$$

The limitations of Eq. (14) are illustrated if we let d = w. Obviously, the equation is not valid when the conductors are touching and the capacitance per unit length becomes infinite. Adding a correction factor, Δt , to d so that we can get infinite capacitance when d = w:

$$\frac{C}{l} = \frac{\pi \epsilon_{\text{Yem}} \epsilon_0}{\ln \left(\frac{\pi (d + \Delta)}{w + t} \right)} F/m, \quad \text{for} \quad \frac{2(w + t)}{\pi d} \leqslant 1$$
 (15)

For infinite capacitance per unit length when d=w;

which means that
$$\left(\frac{\pi(w+\Delta)}{w+I}\right) = 0 \tag{160}$$
Thus Δ is
$$\Delta = \frac{w+I}{\pi} - d$$
Substituting Δ into Eq. (15) yields Eq. (1):
$$\frac{C}{I} = \frac{m^2 + I}{\pi} - d$$
(17)

Pleuse see Section 1.3, Electric Field Mapping, for a discussion on round versus rectangular conductors,

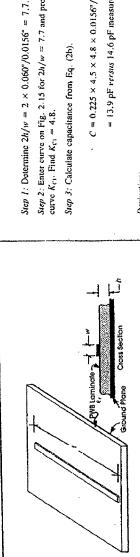
Equations (5), (6a), and (6b) for conductors of unequal width are derived from preceding Eqs. (11) and (14) as applied to Eq. (4) from Formula Set C-1.

Commentary and Conclusions:

- 1. EXP C.5A shows excellent correlation between predicted and measured capacitance values.
- 2. Because the capacitance is governed by the logarithmic term, distance (d) increases do not provide dramatic improvements. If, in Example 1, d is increased from 1" to 2", C decreases to 0.79 pF not by a factor of 2, as might intuitively
- Sometimes, the geometric ratio d/h falls between approximately 1 and a number which is much greater than 1. If the application is critical, it is recommended that an effective dielectric constant, $\epsilon_{\kappa_0 t_0}$, equal to $(1 + \epsilon_s)/2$ be used. In some cases the conductors can be fully embedded in dielectric material as in multilayer circuit boards. In this case, the use of an effective dielectric constant, exem = ε, should be considered.

2.2.6 Capacitance between a Flat Conductor and a Ground Plane, C-6

Ground planes can be used on circuit boards to provide large crosstalk reductions, as we will see later. This formula set gives the capacitance per unit length between a PWB land and the ground plane, as shown in Fig. 2.14.



26

Figure 2.14 A PBW land is located a distance h above a ground plane.

This formula set introduces the relationship between the capacitive fringing factor, K_{c1} , and the inductive fringing factor, K_{c1} . If the medium surrounding the flat conductor and the ground plane is homogeneous, $K_{c1} = K_{c1}$. However, in this case, the flat conductor is separated from the ground plane by the PBW laminate with relative dielectric constant, s., Because the region above the conductor is assumed to have a relative dielectric constant $s_r = 1$, the medium surrounding the conductors is not homogeneous.

Note: The capacitance values found here are not to be confused with mutual capacitance.

Equations:

$$\frac{C}{l} = e_t \varepsilon_0 K_{Cl} \left(\frac{w}{h}\right) F/m$$

 $\widehat{\Xi}$

= 8.84
$$\epsilon K_{CI} \left(\frac{w}{l}\right) PF/m$$
 (2a)
= 0.225 $\epsilon K_{CI} \left(\frac{w}{l}\right) PF/ln$ (2b)

$$= 0.225 \, \varepsilon_r K_{c1} \left(\frac{w}{h}\right) pF/in \tag{}$$

Assume that a 0.0156" wide land is 11" long and is separated from a ground plane by PWB laminate 0.060" thick with relative dielectric constant $\epsilon_r = 4.5$. Compare this value with measured data.

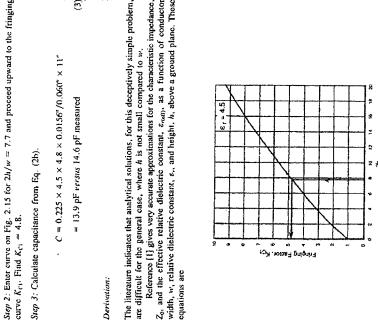


Figure 2.15 in a way similar to Formula Set C.4, the fringing factor, K_{Cr} , is determined by entering the graph at the radiu 2h/w, proceeding upward to the ourve and locating K_{Cr} on the left-hand vertical axis. Thus, for $2h/w \approx 7.7$, $K_{Cr} = 4.8$.

88	
For e, = 1:	Formula Set L-6 and this formula set define L/1 and C/1, respectively, as
$Z_{\Delta(t,-1)} \approx 60 \ln\left(\frac{8h}{w} + \frac{w}{4h}\right) \Omega, \frac{w}{h} \le 1 $ (4)	$\frac{L}{l} \approx \frac{\mu_s \mu_0}{K_{11}} \left(\frac{h}{w} \right) H/m \tag{10}$
$Z_{00,-1} = \frac{120\pi}{\frac{\mu}{h} + 2.42 - 0.44 \left(\frac{h}{h}\right) + \left(1 - \frac{h}{h}\right)^{\delta}} \Omega, \frac{W}{h} \ge 1 \tag{5}$	$\frac{C}{I} = \epsilon_r \epsilon_0 K_{C1} \left(\frac{w}{h}\right) F/m \tag{1}$
where	where $R_{**}=1$ nductive frincing Farrar simuncicalizes
$Z_{\epsilon(t,-1)}=$ characteristic impedance with homogeneous medium and $\epsilon_r=1.$	$K_{Cl} = Capacitive tringing factor, dimensionless K_{Cl} = Capacitive fringing factor, dimensionless$
For the relative dielectric constant, ep.	Combining Eqs. (9), (10) and (11),
$Z_{Q_{C1}} = \frac{Z_{Q_{C1}}}{\sqrt{\epsilon_{\gamma_{C1}}}} \Omega $ (6)	$Z_0 = \frac{1}{\sqrt{K_{Li}K_{ci}}} \sqrt{\frac{\mu_i \mu_0}{\varepsilon_i \varepsilon_0}} \left(\frac{h}{\omega}\right) \Omega \tag{12}$
$Z_{a(c_i)} = cbaracteristic impedance with a dielectric with relative dielectric constant, e., between the flat conductor and the ground plane;$	With $\mu_r = 1$, $\mu_0 = 4\pi \times 10^{-7} \text{ H/m}$ and $\epsilon_0 \approx 10^{-9}/36\pi \text{ F/m}$,
$e_{Aeto} = effective$ relative dielectric constant:	$Z_{Q(c_s)} = \frac{120\pi}{\sqrt{K_{sl}K_{cl}}} \left(\frac{h}{v}\right)\Omega \tag{13}$
$= \frac{c_1 + 1}{2} + \left(\frac{c_1 - 1}{2}\right) \left(\frac{1}{\sqrt{1 + \frac{10h}{w}}}\right) \tag{7}$	As previously stated, if $\varepsilon_r = 1$, the medium between the conductors is homogeneous and therefore $K_{C1} = K_{C1}$. Solving for K_{C1} by letting $Z_0 = Z_{Q(\varepsilon_{r-1})}$ in Eq. (13), we get
Note: s _{tern} in Ref. [1] is changed to s _{rem} to be consistent with notation used in this book.	$Z_{0_{L_{n}},1} = \frac{120\pi}{K_{L_{1}}\sqrt{1}} \left(\frac{h}{w}\right)\Omega$ (14)
	$K_{L1} = \frac{120\pi}{Z_{K_{C}-1}} \binom{h}{w}$ (15)
(6) $a \frac{1}{I} \frac{1}{I} a$ (6)	Note that $K_{L^{j}}$ is dependent only on the relative geometrical dimensions, h and w , and not on the dielectric constant of the material between the flat conductor and the ground plane. K_{C1} is, however, as will be seen in Eq. (16). We can solve for K_{C1} by combining Eqs. (6) and (13) and squaring
making dan mengangan dan dan dan mengangan dan dan dan dan dan dan dan dan dan d	

120π Erecto	$K_{Cl} = \left\{ \frac{1}{Z_{\mathcal{M}_{L} - 1}} \sqrt{\frac{A_{Cl} g_{L}}{K_{Ll} g_{L}}} \left(\frac{1}{W} \right) \right\} \tag{16}$	Table 2.2 lists $Z_{K_{G-13}}$, K_{L_1} and K_{C_1} for various values of w/h using $\varepsilon_r = 4.5$. K_{C_1} for other values of ε_r can be determined in a similar manner. Figure 2.16 plots the capacitive fringing factor, K_{C_1} , versus the geometrical	ratio $2h/w$. $(K_{L1}$ is plotted in Formula Set L_{-6} .) The effective diclocatric constant, ε_{cen} versus $2h/w$ is shown in Fig. 2.17. In Fig. 2.12, we note that the ratio d/w is used for Formula Set C.4. Vertical	Flat Conductors, Pigure 2.18 illustrates the reason for this.	Commentary and Conclusions:	 The solution developed above was easily applied to Pormula Set C-4 because the electric fields are equivalent. 	REFERÊNCES	Schnoider, M.V., "Microstrip Lines for Microwave Integrated Circuits," Bell System Technical Journal, Vol. 48, No. 5 (May-June 1969). Egg. 2
		≅1≥	70	2 2	% 7	% 7 C C C		4. the fringing ratio, 20/1v.
	, = 4.5)	, K	9.30	7.90 5.68	3.14	2.17		anodise or pro
	rersus w/ħ (e	Ku	14.33	12.08 8.51	4.52	2.98 1.92 1.52		to to wood on the state of the
Table 2.2	Fringing Factors K_{Li} , K_{Ci} and $Z_{N_L - ii}$, ϵ_{A_Cii} , $versite$ w/\hbar (e, $=4.5$)	Zeerin A	153.76	145.44	119.66	69.88 25.60 14.62		Figure 2.16 K _{C1} versus 2h/v with 8, a 4.5. This curve indicates that, as would be expected, the fringing flux and hence the fringing factor indicates that, as would be expected, the fringing flux and hence the fringing factor indicates that, as would be expected, the fringing flux and hence the fringing factor indicates that, as would be expected, the fringing flux and hence the fringing factor indicates with increasing bulght 40-width ratio, 2h/v.
	ors Kus Ka	C-1017	2.92	3.58	3.02	5 E E E E		h k, a 4.5.7 fringing to a
1	5 Facto	Zhin nisz	262.94	249.56 221.41	208.06	126.51 78.69 49.64		S S S S S S S S S S S S S S S S S S S
	Fringin	Ž						Fringing Factor, K _{C1}

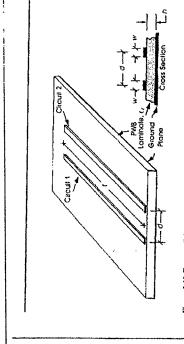


Figure 2.19 Two parallel lands are separated from a ground plane by the circuit board thickness, h.

Figure 2.18 The flux pattern for the upper half of two vertical, flat conductors is identical to that for a single flat conductor over a ground plane. Thus, if we make 2h = d, the correct fringing factor is found in Fig. 2.16.

Ground Plane

Calculate the mutual capacitance between two PWB lands which are 0.025" wide, I" apart, and 6" long on a 0.060" thick board with $\epsilon_r=4.5$. Step 1: Check the ratio 2h/d,

$$\frac{2h}{d} = \frac{2 \times 0.060^{\circ}}{1^{\circ}} = 0.12$$

 $\widehat{\mathfrak{D}}$

which is less than 0.3. If greater, Eq. (9) should be used.

Step 2: Determine the ratio 2h/d

$$\frac{2h}{v} = \frac{2 \times 0.060^{o}}{0.025^{o}} = 4.8$$
 exermine the fringing factors K_{Li} and K_{Ci} from Fig. 2.20 living for C_{ω} from Eq. (2b),

€

Step 3: Determine the fringing factors $K_{\rm Ll}$ and $K_{\rm Cl}$ from Fig. 2.20. Step 4: Solving for C., from Eq. (2b),

$$\frac{C_n}{l} = 0.07 \, e. K_{Ll} K_{Cl} \left(\frac{w}{d}\right)^2 p P / ln$$

$$C_n = 0.07 \times 4.5 \times 5.1 \times 3.5 \times \left(\frac{0.025^n}{l^n}\right)^2 \times 6^n \, p P$$

$$= 0.077 \, n P$$

3

2.2.7 Mutual Capacitance between Two Horizontal, Flat Conductors Near a Ground Plane, C.7

This is perhaps the most important of the capacitance formula sets because it applies directly to single-sided or multilayer printed wiring boards with a ground plane on one side or as a layer. This formula set shows the dramatic reduction in crosstalk provided by the addition of a ground plane. Figure 2.19 illustrates the geometry.

Equations:

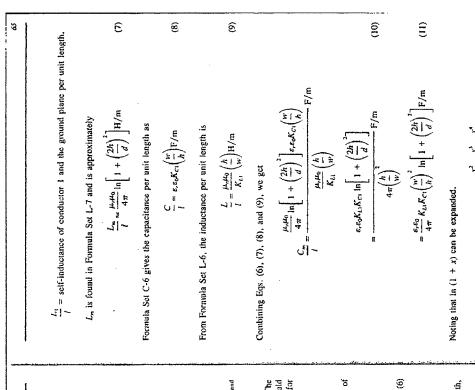
The mutual capacitance/unit length is given approximately by Eq. (1):

$$\frac{C_m}{l} \approx \frac{e_r \epsilon_0}{\pi} K_{L1} K_{C1} \left(\frac{w}{d} \right)^2 F/m, \quad \text{for } \frac{2h}{d} < 0.3 \tag{1}$$

$$= 0.07 \ e_{r}K_{Ll}K_{Ce} \left\{\frac{w}{d}\right\}^{2} \ pF/in \tag{3}$$

= 2.81
$$e_r K_{L1} K_{C1} \left(\frac{w}{d}\right)^2 pF/m$$
 (2a)
= 0.07 $e_r K_{L1} K_{C2} \left(\frac{w}{d}\right)^2 pF/m$ (2b)

(12)



դ ն Ե • « Բրացարգ Բոգու Ալյ

3

Figure 2.20 To find the fringing factors enter the curve at $2\hbar/\nu$ = 4.8 and find $K_{\rm L}$ = 5.1 and $K_{\rm S}$ = 3.5 an the vertical axes.

In the example of Formula Set C-5 for the same geometry, we had 0.90 pF. The improvement gained by adding the ground plane is a factor of 41.3, which would result in a crosstalk reduction of 32.3 dB. Please see EXP C-5 and EXP C-7 for additional details.

Formula Set C-3 gives the mutual capacitance between two circular conductors of equal height over a ground plane as

 $\frac{C_1}{l}$ = capacitance between conductor 1 and the ground plane per unit length, = mutual inductance between conductors over a ground plane per unit length,

This series converges for $-1 < x \le 1$. By neglecting all terms except the first and comparing the value of $\ln (1 + x)$ with x, we find the error to be 14% for x = 0.3, 5% for x = 0.1, at eatera. We can then simplify Eq. (11) by using Eq. (12) with $x = (2h/d)^2$. This procedure produces Eq. (1):

$$\frac{C_n}{l} = \frac{\varepsilon_{L0}}{4\pi} R_{Ll} K_{Cl} \left(\frac{w}{l}\right)^2 \left(\frac{2h}{d}\right)^2$$

$$= \frac{\varepsilon_{L0}}{\pi} K_{Ll} K_{Cl} \left(\frac{w}{d}\right)^2 F/m \tag{13}$$

Commentary and Conclusions:

- 1. The example shows that a ground plane greatly reduces the mutual capacitance and hence crosstalk between two conductors.
- to the ground plane. Thus, the ground plane stays at zero potential with respect 2. As discussed in Formula Set C-3, the return power supply bus land is connected to other circuit land and component voltages.
- Subsection S.2.2, Ground Plane Resistance (R-2) analyzes the "goodness" of the ground plane. The ground plane must be of sufficiently low impedance to 3. Please note that the mutual capacitance is very distance sensitive. Decreasing the spacing by a factor of 10 increases the mutual capacitance by a factor of prevent significant voltages being introduced between operational amplifier-100. Inspection of Eq. (1) indicates this is due to the squared term.
 - the potential at land 2 due to the voltage on land I will be about the same in The derivation of Eq. (1) is based, in part, on expressions for nutual inductance of circular conductors in which only the height above the ground plane, h. and the distance apart, d, are factors. In a way analogous to Formula Set L-7, the assumption is made that the total electric field potential distribution is approximately the same for flat conductors as it is for circular conductors. Thus, summing junctions and the input signal.

2.2.8 Four-Conductor-System Mutual Capacitance, C-8

This formula set has application for determining the mutual capacitance between wiring cable pairs or other four conductor systems. The two circuits are assumed be both ground, and mutually isolated

Formula Set C.-3 gave the value of the mutual capacitance between two conductors in the presence of a ground plane. This formula set solves for the mutual capacitance between two parallel line sets. Effects of shielding are neglected.

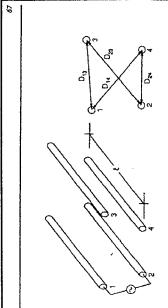


Figure 2.21 Four parallel conductors are spaced at arbitrary distances

Figure 2.21 illustrates the geometry for two conductor pairs with a voltage inpressed between conductors 1 and 2 and voltage pickup appearing on conductors

Equations:

The mutual capacitance per unit length for the conductors shown in Fig. 2.21 (with conductor radii $r_1 = r_2$ and $r_3 = r_3$) is given for $D_{12} \gg 2r_1$, $D_{23} \gg 2r_3$ approximately

$$C_{rr} = \frac{\pi \epsilon_{\epsilon e r_1 \theta_0} \ln \left(\frac{D_{1N} \times D_{2N}}{D_{1N} \times D_{2N}} \right)}{2 \ln \left(\frac{D_{11}}{r_1} \right) \ln \left(\frac{D_{2N}}{r_2} \right)} + F/m \tag{1}$$

$$= 13.9 \epsilon_{t_1 e t_1} \frac{\left(D_{11} \times D_{2N}}{D_{11} \times D_{2N}} \right)}{\ln \left(\frac{D_{11}}{r_1} \right) \ln \left(\frac{D_{2N}}{r_2} \right)} PF/m \tag{2a}$$

$$= 0.35 \epsilon_{t_1 e t_1} \frac{\left(D_{11} \times D_{2N}}{D_{1N} \times D_{2N}} \right)}{\ln \left(\frac{D_{11}}{D_{1N} \times D_{2N}} \right)} PF/m \tag{2b}$$